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ATTY. DOCKET NO. UMC-96-279  
CON  
Client/Matter No. 81848.0016.001

APPLICATION NO.: 09/546,174

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

Sheet 1 of 3

FIRST NAMED INVENTOR:

CHIH-CHIEN LIU

FILING DATE  
APRIL 11, 2000

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Examiner Initials	Cite No.	Document No. No. – Kind Code	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Doc	Class Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Subclass
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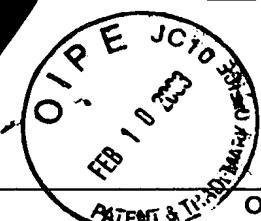
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						YES <input type="checkbox"/> NO <input type="checkbox"/>

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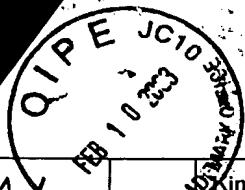
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EXAMINER SIGNATURE	<i>Ruben Bryant</i>	

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